1N6620/U/US thru 1N6625/U/US

ULTRAFAST RECOVERY RECTIFIER

SENSITRON SEMICONDUCTOR

TECHNICAL DATA DATA SHEET 5089, REV. A.3

AVAILABLE AS
1N, JAN, JANTXV
JANS

Ultrafast Recovery Rectifier

Qualified per MIL-PRF-19500/585

- · Hermetic, non-cavity glass package
- Metallurgically bonded
- Operating and storage temperature: -65°C to +175°
- All parts are 100% hot solder dipped
- JAN/ JANTX/ JANTXV available per MIL-PRF-19500/585

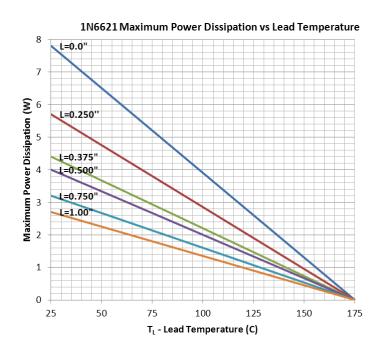
MAX. RATINGS / ELECTRICAL CHARACTERISTICS All ratings are at $T_A = 25^{\circ}$ C unless otherwise specified.

Rating	Symbol	Condition	Max	Units
WORKING PEAK REVERSE VOLTAGE	Symbol	Condition	IVIAX	Offics
1N6620, U, US 1N6621, U ,US 1N6622, U, US 1N6623, U, US 1N6624 ,U, US 1N6625, U, US	V_{RWM}		200 400 600 800 900 1000	Volts
AVERAGE RECTIFIED FORWARD CURRENT 1N6620, U, US thru 1N6622, U, US 1N6623, U, US thru 1N6625, U, US	Io		1.2 1.0	Amps
PEAK FORWARD SURGE CURRENT 1N6620, U, US thru 1N6624,U, US 1N6625, U, US	I _{FSM}	T _p =8.3ms	20 15	A(pk)
MAXIMUM REVERSE CURRENT 1N6620, U, US thru 1N6624,U, US 1N6625, U, US	I _R @ V _{RWM}	T _j = 25 °C	0.5 1.0	μAmps
MAXIMUM REVERSE CURRENT 1N6620, U, US thru 1N6624,U, US 1N6625, U, US	I _R @ V _{RWM}	T _j = 150 °C	150 200	μAmps
MAX. PEAK FORWARD VOLTAGE (PULSED) 1N6620, U, US thru 1N6622,U, US 1N6623,U, US & 1N6624,U, US 1N6625, U, US	V _{FM}	I _F =2.0A I _F =1.5μA I _F =1.5μA	1.60 1.80 1.95	Volts
PEAK RECOVERY CURRENT 1N6620, U, US thru 1N6622,U, US 1N6623,U, US & 1N6624,U, US 1N6625, U, US	I _{RM}	I _F =2A, 100A/μ	3.5 4.2 5.0	A(pk)
MAXIMUM REVERSE RECOVERY TIME 1N6620, U, US thru 1N6622,U, US 1N6623,U, US & 1N6624,U, US 1N6625, U, US	T _{rr}	I _F =0.5A I _{RM} =1.0A	30 50 60	ns
FORWARD RECOVERY VOLTAGE 1N6620, U, US thru 1N6622,U, US 1N6623,U, US & 1N6624,U, US 1N6625, U, US	V _{FRM}	I _F =0.5A t _r =12ns	12 18 30	Volts
THERMAL RESISTANCE (Axial) 1N6620 thru 1N6625	$R\theta_{JL}$	L=.375	38	°C/W
THERMAL RESISTANCE (MELF) 1N6620U,US thru 1N6625U,US	$R\theta_{JEC}$	L=0	13	°C/W

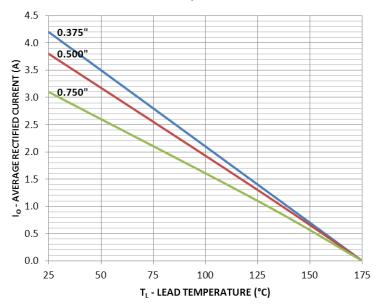
^{*}Sensitron equivalent diodes are manufactured and screened to MIL-PRF-19500 flow and guidelines starting from wafer fabrication through assembly and testing using our specification 7700-4093.

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1N6621 Maximum Current vs Lead Temperature (Power @ T_i = +175°C)

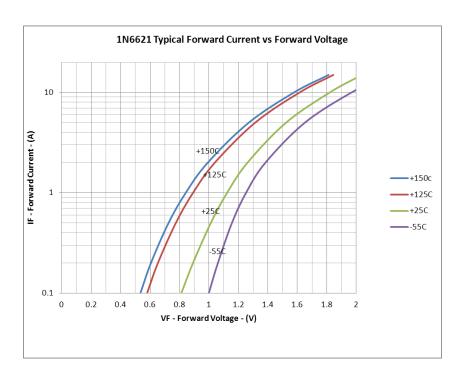


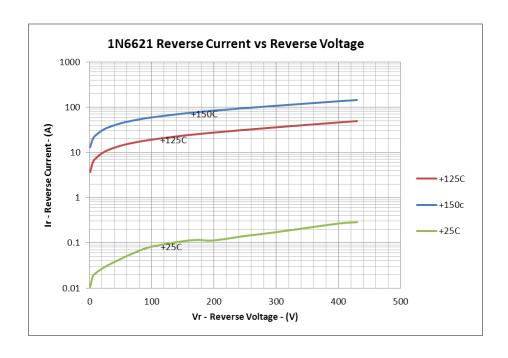


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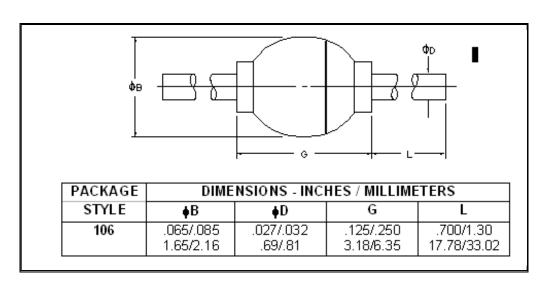


ULTRAFAST RECOVERY RECTIFIER

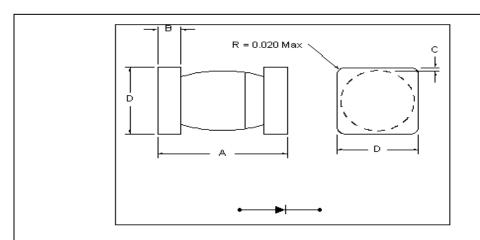
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MECHANICAL DIMENSIONS In Inches / (mm)

AXIAL



MELF (Add "U" or "US" to Part Number)



PACKAGE	DIMENSIONS - INCHES / MILLIMETERS			
STYLE	Α	В	С	D
MELF-A	.168/.200	0.019/.028	.003 Min	.091/.103
	4.27/5.08	.48/.71	.08 Min	2.31/2.62

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The following part numbers can be purchased in either axial or surface mount devices and screened and tested to the military screening flow. The parts are marked in accordance with the testing performed, example:

	<u> </u>		
Sensitron Screening Level	*Part Number	*Part Number	
	Leaded Package	MELF Package	
	(example for 1N6620)	(example for 1N6620)	
1N	1N6620	1N6620US or 1N6620US	
JAN	JAN1N6620	JAN1N6620US or JAN1N6620U	
JANTX	JANTX1N6620	JANTX1N6620US or JANTX1N6620U	
JANTXV	JANTXV1N6620	JANTXV1N6620US or JANTXV1N6620U	
JANS	JANS1N6620	JANS1N6620US or JANS1N6620U	

^{*}Parts can also be ordered Tape & Reel

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